	Туре	Hits	Search Text	DB	Bs
<u></u>	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "ohmic layer" and "reflector layer"	USPAT	
2	BRS	0	"light emitting device" and semiconductor and "p-type layer" and "n-type layer" and "ohmic layer" and "reflector layer"	USPAT	I
ω	BRS	0	"light emitting device" and semiconductor and "p-type layer" and "ohmic layer" and "reflector layer"	USPA	H
4	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "reflector layer"	USPA	Ť
5	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "n-type layer"	USPA	ĄΤ
9	BRS	⊢ ¹	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer"	USPA	ΔT
7	BRS	0	light emitting device" and emiconductor and "ohmic lap-type layer" and "reflect	USPA	TI
8	BRS	13	"light emitting device" and semiconductor and "ohmic layer"	USPA	AT
9	BRS	0	ce" hmic mirr	USPA	PAT
10	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "reproducer layer"	USPA	PAT

	Type	Hits	Search Text	DBs	Time Stamp	Comments
11	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "replicator layer"	USPAT	2001/03/12 10:24	
12	BRS	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer" and "replicator layer"	USPAT	2001/03/12 10:24	
13	BRS .	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer" and "replicate layer"	USPAT	2001/03/12 10:24	
14	BRS	0	divice" and nd "ohmic layer" and "replicate l	USPAT	2001/03/12 10:25	
15	BRS	0	"light emitting divice" and semiconductor and "ohmic layer" and "p-type layer" and "replicate"	USPAT	2001/03/12 10:25	
16	BRS	0	"light emitting divice" and semiconductor and "ohmic layer" and "p-type layer" and "mirror"	USPAT	2001/03/12 10:26	
17	BRS	0	"light emitting divice" and semiconductor and "ohmic layer" and "p-type layer" and "reproduce"	USPAT	2001/03/12 10:26	
18	BRS	0	and nd "o r"	USPAT	2001/03/12 10:27	
19	BRS	0	g divi type]	USPAT	2001/03/12 10:27	
20	BRS	0	emitting div nductor and " e layer"	USPAT	2001/03/12 10:27	
21	BRS.	₽	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer"	USPAT	2001/03/12 10:29	
22	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and replicator	USPAT	2001/03/12 10:29	

	Туре	Hits	Search Text	DBs	Time Stamp
23	BRS	⊣	emitting device" nductor and "ohmic adj layer	USPAT	2001/03/12 10:29
24	BRS	0	emitting device" nductor and "ohmic adj layer and rep	USPAT	2001/03/12 10:30
25	BRS	0	"light emitting device" and semiconductor adj layer and "ohmic layer" and p-type adj layer	USPAT	2001/03/12 10:30
26	BRS	Н	መ ጠ :	USPAT	2001/03/12 10:32
27	BRS	Ъ .	"light emitting device" and semiconductor adj layers and "ohmic layer" and p-type adj layer	USPAT; EPO; JPO; Derwent; IBM	USPAT; EPO; JPO; Derwent 2001/03/12 10:32 ; IBM ; IBM
28	BRS	13035	"light emitting device"	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:33
29	BRS	671	"light emitting device" and semiconductor adj layers	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:34
30	BRS	125	"light emitting device" and semiconductor adj layers and p-type adj layer	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:34

36 E	3.5 E	34	33	32 E	31 E	
BRS	BRS	BRS	BRS	BRS	BRS	Туре
0 .	0	707	2202163	. 0	87	Hits
"light emitting device" and semiconductor adj layers and p-type adj layer and "ohmic layer"	"light emitting device" and semiconductor adj layers and p-type adj layer and reflector adj layer and reflector adj layer and reflector adj layer and reflector adj layer and	"light emitting device" and semiconductor adj layers and p-type adj layer and reflector layer and "ohmic layer"	"light emitting device" and semiconductor adj layers and p-type adj layer and reflector layer	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector adj layer	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer	Search Text
USPAT; EPO; JPO; Derwent; IBM	USPAT; EPO; JPO; Derwent; IBM TDB	T; ent	USPAT; EPO; JPO; Derwent; IBM TDB	USPAT; EPO; JPO; Derwent ; IBM TDB	USPAT; EPO; JPO; Derwent; IBM	DBs
2001/03/12 10:41	2001/03/12 10:40	2001/03/12 10:39	2001/03/12 10:39	2001/03/12 10:38	USPAT; EPO; JPO; Derwent 2001/03/14 13:31 ; IBM TDB	Time Stamp
			-			Comments

	42 E	41 E	40 E	39	38	37 I	
	BRS	BRS	BRS	BRS	BRS	BRS.	Туре
	0	0	0	. 0	9	2	Hits
	"light emitting device" and semiconductor adj layers and p-type adj layer and ohmic and replicate	"light emitting device" and semiconductor adj layers and p-type adj layer and ohmic and replicator	"light emitting device" and semiconductor adj layers and p-type adj layer and ohmic and reproduce	"light emitting device" and semiconductor adj layers and p-type adj layer and ohmic and reproducer	"light emitting device" and semiconductor adj layers and p-type adj layer and ohmic and mirror	"light emitting device" and semiconductor adj layers and p-type adj layer and ohmic and reflect	Search Text
,	USPAT; EPO; JPO; Derwent; IBM	USPAT; EPO; JPO; Derwent; IBM	nt	USPAT; EPO; JPO; Derwent; IBM	USPAT; EPO; JPO; Derwent; IBM TDB	USPAT; EPO; JPO; Derwent; IBM TDB	DBs
***************************************	2001/03/12 10:48	2001/03/12 10:48	2001/03/12 10:48	2001/03/12 10:48	2001/03/12 10:48	USPAT; EPO; JPO; Derwent 2001/03/12 10:43 ; IBM ; IBM	Time Stamp
Treatment of the second							Comments

Search Te	"light emitting device" and semiconductor adj layers and p-type adj layer and ohmic and contact adj resistance	"light emitting device" and semiconductor adj layers and p-type adj layer and ohmic and contact adj resistance	"light emitting device" and semiconductor adj layers and p-type adj layer and ohmic and contact adj resistance
ng de adj n-ty tact adj adj adj adj	ng device" and adj layers and p-type n-type adj layer and tact adj resistance ng device" and adj material and "p-type	ng device" and adj layers and p-type n-type adj layer and tact adj resistance ng device" and adj material and "p-type	ng device" and adj layers and p-type n-type adj layer and tact adj resistance ng device" and adj material and "p-type
rice" ar ayers a de adj resi	id p-type ind p-type ind stance ind stance ind stance ind and "p-type and "ohmic"	USPAT; Ind p-type JPO; Layer and Derwent Stance ; IBM TDB Id TDB and "p-type USPAT and "ohmic	USPAT; Ind p-type JPO; ayer and Derwent 2001/03/13 11: stance TDB Id and "p-type USPAT 2001/03/14 13: and "ohmic USPAT 2001/03/14 13:

	Туре	Hits	Search Text	DBs	Time Stamp	Comments
64	BRS	0		USPAT	2001/03/14 18:13	:
65	BRS	6	5351255.PN. OR 5585648.PN. OR 5932896.PN. OR 6190937.PN. OR 6057565.PN. OR 5990500.PN.		JSPAT 2001/03/14 18:13	

	Туре	Hits	Search Text	DBs	Time Stamp
1	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and "ohmic layer" and "reflector layer"	EPO; JPO;	
2	BRS	4	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and ohmic and reflector	EPO;	
3	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and ohmic and reflector	JPO; Derwen	2001/03/15 09:38
4	BRS	0	. "light emitting device" and "p-type layer" and "n-type layer" and ohmic and reflector	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:38
5	BRS	0	"n-type layer" and ohmic	.TPO•	2001/03/15 09:39
6	BRS	0	"light emitting device" and semiconductor adj material and "p-type" and "n-type" and ohmic and mirror	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:39
7	BRS	0	semiconductor adj material and "p-type" and "n-type" and and obmic and mirror	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:39

	Туре	Hits	Search Text	DBs	Time Stamp
8	BRS	0	"light emitting device" and semiconductor adj material and "multi layers" and ohmic and mirror	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:40
9	BRS	0	"light emitting device" and semiconductor and "multi layers" and ohmic and mirror	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:40
10	BRS	0	"light emitting device" and semiconductor and "multi layers" and mirror	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:41
11	BRS	0	"light emitting device" and "multi layers" and mirror and ohmic	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:41
12	BRS	0	"light emitting device"	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:41
13	BRS	8576	"light emitting device"	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:41
14	BRS	6	"light emitting device" and ohmic adj layer	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:42
15	BRS	0	"light emitting device" and ohmic adj layer and reflector	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:42

	Туре	Hits	Search Text	DBs	Time Stamp
16	BRS	0	I .	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:42
17	BRS	1	"light emitting device" and ohmic and mirror	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:42